

S/N Unknown

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Jerome M. Eldridge et al.	Examiner:	Unknown
Serial No.:	Unknown	Group Art Unit:	Unknown
Filed:	Herewith	Docket:	1303.063US2
Title:	GRADED COMPOSITION METAL OXIDE TUNNEL BARRIER INTERPOLY INSULATORS		

INFORMATION DISCLOSURE STATEMENT

Mail Stop Patent Application
Commissioner for Patents
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In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Information Disclosure Statement.

Pursuant to 37 C.F.R. §1.98(d), copies of the listed documents are not provided as these references were previously cited by or submitted to the U.S. Patent Office in connection with Applicants' prior U.S. application, Serial No. 10/177096, filed on June 21, 2002, which is relied upon for an earlier filing date under 35 U.S.C. §120.

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Serial No :Unknown

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The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

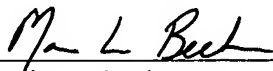
Respectfully submitted,

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STATEMENT BY APPLICANT**

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First Named Inventor	Eldridge, Jerome
Group Art Unit	Unknown
Examiner Name	Unknown

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US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
	US-2001/0013621	08/16/2001	Nakazato, K.	257	314	12/08/2000
	US-2001/0055838	12/27/2001	Walker, A J., et al.	438	129	08/13/2001
	US-2002/0028541	03/07/2002	Lee, T H., et al.	438	149	08/13/2001
	US-2002/0106536	08/08/2002	Lee, Jongho, et al.	428	702	02/02/2001
	US-2002/0137250	09/26/2002	Nguyen, B., et al.	438	53	03/15/2002
	US-4,295,150	10/13/1981	Adam, Fritz	357	54	10/01/1979
	US-4,412,902	11/01/1983	Michikami, Osamu, et al.	204	192	06/18/1982
	US-4,757,360	07/12/1988	Faraone, Lorenzo, et al.	357	23.5	07/06/1983
	US-4,780,424	10/25/1988	Holler, Mark A., et al.	437	29	09/28/1987
	US-5,691,230	11/25/1997	Forbes, Leonard	437	62	09/04/1996
	US-5,042,011	08/20/1991	Casper, Stephen L., et al.	365	205	05/22/1989
	US-5,071,782	12/10/1991	Mori, Kiyoshi	437	48	06/28/1990
	US-5,073,519	12/01/1991	Rodder, Mark	438	269	10/31/1990
	US-5,280,205	06/18/1994	Green, Robert S., et al.	307	530	04/16/1992
	US-5,350,738	09/27/1994	Hase, Takashi, et al.	505	473	11/27/1992
	US-5,399,516	03/21/1995	Bergendahl, A., et al.	437	43	09/21/1992
	US-5,418,389	05/23/1995	Watanabe, Y.	257	295	11/09/1993
	US-5,497,494	03/05/1996	Combs, J, et al.	395	750	07/23/1993
	US-5,498,558	03/12/1996	Kapoor, A	437	43	05/06/1994
	US-5,508,544	04/16/1996	Shah, P. L.	257	316	09/27/1994
	US-5,600,592	02/04/1997	Atsumi, S., et al.	365	185.18	05/08/1995
	US-5,618,575	04/08/1997	Peter, Gunter	427	8	04/21/1995
	US-5,619,642	04/08/1997	Nielsen, M, et al.	395	182.04	12/23/1994
	US-5,627,785	05/06/1997	Gilliam, Gary R., et al.	365	189.01	03/15/1996
	US-5,677,867	10/14/1997	Hazani, E.	365	185	06/30/1995
	US-5,691,209	11/25/1997	Liberkowsky, J B.	437	7	10/15/1996
	US-5,691,230	11/25/1997	Forbes, Leonard	437	62	09/04/1996
	US-5,739,544	04/14/1998	Yuki, K, et al.	257	25	12/12/1995
	US-5,801,401	09/01/1998	Forbes, Leonard	257	77	01/29/1997
	US-5,852,306	12/22/1998	Forbes, Leonard	257	315	01/29/1997
	US-5,880,991	03/09/1999	Hsu, L., et al.	365	182	04/14/1997
	US-5,923,056	07/13/1999	Lee, Woo-Hyeong, et al.	257	192	03/12/1998
	US-5,936,274	08/10/1999	Forbes, Leonard, et al.	257	315	07/08/1997
	US-5,952,692	09/14/1999	Nakazato, Kazuo, et al.	257	321	10/28/1997
	US-5,981,350	11/09/1999	Geusic, Joseph E., et al.	438	386	05/29/1998

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First Named Inventor	Eldridge, Jerome
Group Art Unit	Unknown
Examiner Name	Unknown

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Attorney Docket No: 1303.063US2

	US-5,986,932	11/16/1999	Ratnakumar, K. N., et al.	365	185.07	06/30/1997
	US-5,991,225	11/23/1999	Forbes, Leonard, et al.	365	230.06	02/27/1998
	US-6,025,228	02/15/2000	Ibok, E., et al.	438	261	11/25/1997
	US-6,025,627	02/15/2000	Forbes, Leonard, et al.	257	321	05/29/1998
	US-6,031,263	02/29/2000	Forbes, Leonard, et al.	257	315	07/29/1997
	US-6,069,380	05/30/2000	Chou, S.Y., et al.	257	315	07/25/1997
	US-6,069,816	05/30/2000	Nishimura, Kiyoshi	365	145	11/24/1998
	US-6,077,745	06/20/2000	Burns, Jr., S. M., et al.	438	270	10/29/1997
	US-6,124,729	09/26/2000	Noble, Wendell P., et al.	326	41	02/27/1998
	US-6,134,175	10/17/2000	Forbes, Leonard, et al.	365	230.06	08/04/1998
	US-6,135,175	10/24/2000	Gaudreault, P., et al.	144	4.1	10/19/1998
	US-6,141,238	10/31/2000	Forbes, L., et al.	365	145	08/30/1999
	US-6,141,248	10/31/2000	Forbes, et al.	365	185.08	07/29/1999
	US-6,143,636	11/07/2000	Forbes, Leonard, et al.	438	587	08/20/1998
	US-6,153,468	11/28/2000	Forbes, Leonard, et al.	438	257	05/17/1999
	US-6,163,049	12/19/2000	Bui, N. D.	257	321	10/13/1998
	US-6,208,164	03/27/2001	Noble, Wendell P., et al.	326	41	08/04/1998
	US-6,210,999	04/03/2001	Gardner, Mark I., et al.	438	183	12/04/1998
	US-6,229,175	05/08/2001	Uchida, Hidetsugu	257	315	03/19/1999
	US-6,238,976	05/29/2001	Noble, Wendell P., et al.	438	259	02/27/1998
	US-6,246,606	06/12/2001	Forbes, Leonard, et al.	365	185.03	09/02/1999
	US-6,249,020	06/19/2001	Forbes, Leonard, et al.	257	315	08/27/1998
	US-6,249,460	06/19/2001	Forbes, Leonard, et al.	365	185.28	02/28/2000
	US-6,306,708	10/23/2001	Peng, N.	438	266	02/02/2000
	US-6,307,775	10/23/2001	Forbes, Leonard, et al.	365	185.01	08/27/1998
	US-6,323,844	11/27/2001	Yeh, Fu-Kuo, et al.	345	166	08/11/1997
	US-6,351,411	02/26/2002	Forbes, Leonard, et al.	365	182	06/12/2001
	US-6,424,001	07/23/2002	Forbes, Leonard, et al.	257	315	02/09/2001
	US-6,433,382	08/13/2002	Orlowski, M., et al.	257	315	04/06/1995
	US-6,461,931	10/08/2002	Eldridge, Jerome M.	438	398	08/29/2000
	US-6,475,857	11/05/2002	Kim, Woosik, et al.	438	240	06/21/2001
	US-6,541,280	04/01/2003	Kaushik, Vidya S., et al.	438	3	03/20/2001
	US-6,586,797	07/01/2003	Forbes, Leonard, et al.	257	325	08/30/2001

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T ²
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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		AARIK, JAAN, et al., "Anomalous effect of temperature on atomic layer deposition of titanium oxide", Journal of Crystal Growth, (2000), pp. 531-537	

EXAMINER**DATE CONSIDERED**

Substitute Disclosure Statement Form (PTO-1449)

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>	Complete if Known	
	Application Number	Unknown
	Filing Date	Even Date Herewith
	First Named Inventor	Eldridge, Jerome
	Group Art Unit	Unknown
	Examiner Name	Unknown
Sheet 3 of 6	Attorney Docket No: 1303.063US2	

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		AARIK, JAAN, et al., "Texture development in nanocrystalline hafnium dioxide thin films grown by atomic layer deposition", <u>Journal of Crystal Growth</u> , 220(1-2), (2000), 105-113	
		AFANAS'EV, V., et al., "Electron energy barriers between (100)Si and ultrathin stacks of SiO ₂ , Al ₂ O ₃ , and ZrO ₃ and ZrO ₂ insulators", <u>Applied Physics Letters</u> , 78(20), (2001), pp. 3073-3075	
		ARYA, S., et al., "Conduction Properties of Thin Al ₂ O ₃ Films", <u>Thin Solid Films</u> , 91, (1982), 363-374	
		DIPERT, BRIAN, "Flash Memory Goes Mainstream", <u>IEEE Spectrum</u> , 30(10), (October 1993), 48-52	
		EIERDAL, L., et al., "Interaction of oxygen with Ni(110) studied by scanning tunneling microscopy", <u>Surface Science</u> , 312, (1994), pp. 31-53	
		ELDRIDGE, J., et al., "Analysis of Ultrathin Oxide Growth on Indium", <u>Thin Solid Films</u> , 12, (1972), pp. 447-451	
		ELDRIDGE, J., et al., "Measurement of Tunnel Current Density in a Metal-Oxide-Metal System as a Function of Oxide Thickness", <u>Proc. 12th Intern. Conf. on Low Temperature Physics</u> , (1971), 427-428	
		ELDRIDGE, J.M., et al., "The Growth of Thin PbO Layers on Lead Films", <u>Surface Science Vol. 40</u> , (1973), 512-530	
		FERGUSON, J D., et al., "Atomic layer deposition of Al ₂ O ₃ and SiO ₂ on BN particles using sequential surface reaction", <u>Applied Surface Science</u> , (2000), pp. 280-292	
		GREINER, J., "Josephson Tunneling Barriers by rf Sputter Etching in an Oxygen Plasma", <u>Journal of Applied Physics</u> , 42(12), (November 1971), 5151-5155	
		GREINER, J., "Oxidation of lead films by rf sputter etching in an oxygen plasma", <u>Journal of Applied Physics</u> , 45(1), (1974), 32-37	
		GRIMBLOT, J., et al., "I. Interaction of Al films with O ₂ at low pressures", <u>J. Electro. Chem. Soc.</u> , Vol. 129, No. 10, (1982), pp. 2366-2368	
		GRIMBLOT, J., et al., "II. Oxidation of Aluminum Films", <u>J. Electrochem.</u> , 129, (1982), pp. 2369-2372	
		GUNDLACH, K., et al., "Logarithmic Conductivity of Al-Al ₂ O ₃ -Al Tunneling Junctions Produced by Plasma and by Thermal Oxidation", <u>Surface Science</u> , 27, (1971), 125-141	
		GUO, X., "High Quality Ultra-thin (1.5 nm) TiO ₂ /Si ₃ N ₄ Gate Dielectric for Deep Sub-micron CMOS Technology", <u>IEDM Technical Digest</u> , (1999), pp. 137-140	
		HODGES, D. A., et al., <u>Analysis and Design of Digital Integrated Circuits</u> , McGraw-Hill Book Company, 2nd Edition, (1988), 394-396	
		HODGES, D. A., <u>Analysis and Design of Digital Integrated Circuits</u> , 2nd Edition, McGraw-Hill Publishing. New York, (1988), pp. 354-357	

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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

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		HURYCH, Z., "Influence of Non-Uniform Thickness of Dielectric Layers on Capacitance and Tunnel Currents", <u>Solid-State Electronics</u> , vol. 9, (1966), 967-979	
		ITOKAWA, H., "Determination of Bandgap and Energy Band Alignment for High-Dielectric-Constant Gate Insulators Using High-Resolution X-ray Photoelectron Spectroscopy", <u>Extended Abstracts of the 1999 International Conference on Solid State Devices and Materials</u> , (1999), pp. 158-159	
		KIM, YONG S., et al., "Effect of rapid thermal annealing on the structure and the electrical properties of atomic-layer-deposited Ta2O5 films", <u>Journal of the Korean Physical Society</u> , (December 2000), pp. 975-979	
		KIM, H., "Leakage current and electrical breakdown in metal-organic chemical vapor deposited TiO2 dielectrics on silicon substrates", <u>Applied Phys. Lett.</u> , 69(25), (1996), pp. 3860-3862	
		KIM, YEONG K., et al., "Novel capacitor technology for high density stand-alone and embedded DRAMs", <u>IEEE</u> , (2000), pp. 369-372	
		KUBASCHEWSKI, O., et al., <u>Oxidation of Metals and Alloys, Second Edition</u> , Butterworths, London, (1962), pp. 1-3, 5,6, 8-12, 24, 36-39	
		KUBASCHEWSKI, O., et al., "Oxidation of Metals and Alloys", <u>Butterworths</u> , London, (1962), 53-63	
		KUKLI, KAUPO, "Atomic Layer Deposition of Titanium Oxide from TiI4 and H2O2", <u>Chemical Vapor Deposition</u> , 6(6), (2000), 303-310	
		KUKLI, KAUPO, et al., "Atomic layer deposition of zirconium oxide from zirconium tetraiodide, water and hydrogen peroxide", <u>Journal of Crystal Growth</u> , (2001), pp. 262-272	
		KUKLI, K., "Development of Dielectric Properties of Niobium Oxide, Tantalum Oxide, and Aluminum Oxide Based Nanolayered Materials", <u>Journal of the Electrochemical Society</u> , 148(2), (2001), pp. F35-F41	
		KUKLI, KAUPO, et al., "Real-time monitoring in atomic layer deposition of TiO2 from TiI4 and H2O-H2O2", <u>American Chemical Society</u> , (2000), pp. 8122-8128	
		KWO, J., "Properties of high k gate dielectrics Gd2O3 and Y2O3 for Si", <u>Journal of Applied Physics</u> , 89(7), (2001), pp. 3920-3927	
		LEE, J., "Effect of Polysilicon Gate on the Flatband Voltage Shift and Mobility Degradation for ALD-Al2O3 Gate Dielectric", <u>IEDM</u> , (2000), pp. 645-648	
		LUAN, H. F., "High Quality Ta2O5 Gate Dielectrics with Tox,eq<10A", <u>IEDM Technical Digest. International Electron Devices Meeting</u> , (December 5-8, 1999), 141-143	
		MA, Y., "Zirconium Oxide Based Gate Dielectrics with equivalents Oxide Thickness of Less Than 1.0 nm and Performance of Submicron MOSFET using a Nitride Gate Replacement Process", <u>IEDM - Technical Digest</u> , (1999), pp. 149-152	

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		MARSHALEK, R., et al., "Photoresponse Characteristics of Thin-Film Nickel-Nickel Oxide-Nickel Tunneling Junctions", <u>IEEE Journal of Quantum Electronics</u> , QE-19(4), (1983), pp. 743-754	
		MASUOKA, F., et al., "A 256K Flash EEPROM using Triple Polysilicon Technology", <u>IEEE International Solid-State Circuits Conference, Digest of Technical Papers</u> , (1985), 168-169	
		MASUOKA, F., et al., "A New Flash EEPROM Cell using Triple Polysilicon Technology", <u>International Electron Devices Meeting, Technical Digest</u> , San Francisco, CA, (1984), 464-467	
		MORI, S., et al., "Reliable CVD Inter-Poly Dielectrics for Advanced E&EEPROM", <u>Symposium on VLSI Technology, Digest of Technical Papers</u> , (1985), 16-17	
		MULLER, H., "Electrical and Optical Properties of Sputtered In2O3 Films", <u>Physica Status Solidi</u> , 27(2), (1968), pp.723-731	
		PARANJPE, AJIT, et al., "Atomic layer deposition of AlOx for thin film head gap applications", <u>Journal of the Electrochemical Society</u> , (September 2001), pp. 465-471	
		PASHLEY, R., et al., "Flash Memories: the best of two worlds", <u>IEEE Spectrum</u> , 26(12), (December 1989), 30-33	
		POLLACK, S., et al., "Tunneling Through Gaseous Oxidized Films of Al2O3", <u>Transactions of the Metallurgical Society of AIME</u> , 233, (1965), 497-501	
		QI, W., "MOSCAP and MOSFET characteristics using ZrO2 gate dielectric deposited directly on Si", <u>IEDM - Technical Digest</u> , (1999), 145-148	
		ROBERTSON, J., "Band offsets of wide-band-gap oxides and implications for future electronic devices", <u>Journal of Vacuum Science & Technology B (Microelectronics and Nanometer Structures)</u> , 18(3), (May-June 2000), 1785-1791	
		ROBERTSON, J., et al., "Schottky Barrier height of Tantalum oxide, barium strontium titanate, lead titanate, and strontium bismuth tantalate", <u>Applied Physics Letters</u> , vol. 74, no. 8, (02/22/1999), 1168-1170	
		SHI, Y., "Tunneling Leakage Current in Ultrathin (<4 nm) Nitride/Oxide Stack Dielectrics", <u>IEEE Electron Device Letters</u> , 19(10), (Oct. 1998), pp. 388-390	
		SIMMONS, J., "Generalized Formula for the Electric Tunnel Effect between Similar Electrodes Separated by a Thin Insulating Film", <u>Journal of Applied Physics</u> , 34(6), (1963), 1793-1803	
		SMITH, RYAN C., et al., "Chemical vapour deposition of the oxides of titanium, zirconium and hafnium for use as high-k materials in microelectronic devices. A carbon-free precursor for the synthesis of hafnium dioxide", <u>Advanced Materials for Optics and Electronics</u> , (2000), 105-114	
		SWALIN, R., "Equilibrium between Phases of Variable Composition", <u>Thermodynamics of Solids</u> , 2nd Edition, (1972), pp. 165-180	

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		SZE, S., "Physics of Semiconductor Devices, Second Edition", <u>John Wiley & Sons, New York, (1981),553-556</u>	
		YAN, J., "Structural and electrical characterization of TiO2 grown from titanium tetrakis-isopropoxide (TTIP) and TTIP/H2O ambients", <u>Journal of Vacuum Science Technology B 14(3), (1996), pp. 1706-1711</u>	
		ZHANG, H., et al., "Atomic Layer Deposition of High Dielectric Constant Nanolaminates", <u>Journal of The Electrochemical Society, 148(4),(2001), F63-F66</u>	

EXAMINER**DATE CONSIDERED**

Substitute Disclosure Statement Form (PTO-1449)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached